

Tanmoy Basu

List of Publications by Year in descending order

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Version: 2024-02-01

24
papers

309
citations

933447

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888059

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24
all docs

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docs citations

24
times ranked

208
citing authors

#	ARTICLE	IF	CITATIONS
1	Transition from ripples to faceted structures under low-energy argon ion bombardment of silicon: understanding the role of shadowing and sputtering. <i>Nanoscale Research Letters</i> , 2013, 8, 289.	5.7	50
2	Unusual pattern formation on Si(100) due to low energy ion bombardment. <i>Applied Surface Science</i> , 2012, 258, 9944-9948.	6.1	33
3	Ultra-violet absorption induced modifications in bulk and nanoscale electrical transport properties of Al-doped ZnO thin films. <i>Journal of Applied Physics</i> , 2015, 118, .	2.5	29
4	Thickness-dependent blue shift in the excitonic peak of conformally grown ZnO:Al on ion-beam fabricated self-organized Si ripples. <i>Journal of Applied Physics</i> , 2015, 118, .	2.5	26
5	Temporal evolution of Ge surface topography under keV ion irradiation: Combined effects of curvature-dependent sputter erosion and atomic redistribution. <i>Applied Surface Science</i> , 2016, 360, 131-142.	6.1	22
6	Thickness-controlled photoresponsivity of ZnO:Al/Si heterostructures: Role of junction barrier height. <i>Materials Letters</i> , 2014, 135, 188-190.	2.6	17
7	Tunable antireflection from conformal Al-doped ZnO films on nanofaceted Si templates. <i>Nanoscale Research Letters</i> , 2014, 9, 192.	5.7	15
8	Nanostructures on GaAs surfaces due to 60keV Ar ⁺ -ion beam sputtering. <i>Applied Surface Science</i> , 2012, 258, 4144-4147.	6.1	14
9	Tailoring room temperature photoluminescence of antireflective silicon nanofacets. <i>Journal of Applied Physics</i> , 2014, 116, 114309.	2.5	13
10	Temporal evolution of ripple pattern on silicon surface: An ion induced solid flow approach. <i>Applied Surface Science</i> , 2014, 310, 142-146.	6.1	11
11	Surfing Silicon Nanofacets for Cold Cathode Electron Emission Sites. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 38931-38942.	8.0	10
12	Modification of structural and dielectric properties of polycrystalline Gd-doped BFO/PZO. <i>Journal of Advanced Dielectrics</i> , 2018, 08, 1850031.	2.4	9
13	Temporal evolution on SiO ₂ surface under low energy Ar ⁺ -ion bombardment: roles of sputtering, mass redistribution, and shadowing. <i>Journal of Physics Condensed Matter</i> , 2018, 30, 334001.	1.8	9
14	Formation of self-organized nanostructures on semi-insulating InP by 100keV Ar ⁺ -ion irradiation. <i>Applied Surface Science</i> , 2012, 258, 4139-4143.	6.1	7
15	Evolution of ripple morphology on Si(100) by 60-keV argon ions. <i>Applied Surface Science</i> , 2012, 258, 4135-4138.	6.1	7
16	Statistical analysis of ripple morphology on Si surfaces due to 60 keV Ar ⁺ -ions. <i>Surface Topography: Metrology and Properties</i> , 2016, 4, 015002.	1.6	7
17	Local probe microscopic studies on Al-doped ZnO: Pseudoferroelectricity and band bending at grain boundaries. <i>Journal of Applied Physics</i> , 2016, 119, .	2.5	6
18	Temporal evolution of a silicon surface subject to low energy ion irradiation and concurrent sample rotation. <i>Applied Surface Science</i> , 2016, 379, 480-488.	6.1	6

#	ARTICLE	IF	CITATIONS
19	Cold cathode electron emission with ultralow turn-on fields from Au-nanoparticle-decorated self-organized Si nanofacets. Journal of Materials Chemistry C, 2020, 8, 16880-16895.	5.5	6
20	Evolution Of Surface Topography On GaAs(100) And GaAs(111) At Normal And Oblique Incidence Of Ar ⁺ -ions. , 2010, , .		3
21	Evolution of microstructure and surface topography of gold thin films under thermal annealing. , 2012, , .		3
22	Probing local work function of electron emitting Si-nanofacets. Applied Surface Science, 2017, 418, 340-345.	6.1	3
23	Considerations for the nano aperture ion source: Geometrical design and electrical control. Review of Scientific Instruments, 2020, 91, 013310.	1.3	2
24	Ion erosion induced nanostructured semiconductor surfaces. International Journal of Nanotechnology, 2012, 9, 1007.	0.2	1